

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Inventors: Wei Gao, and Yoshi Ono

Serial No: Not Yet Assigned

Filed: Herewith

Title: MOSFET STRUCTURES WITH
CONDUCTIVE NBO GATES

PATENT APPLICATION

Attorney Docket No.
SLA0805

Hon. Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

September 30, 2003
(Date)

Respectfully submitted,



Matthew D. Rabdau
Reg. No. 43,026

Matthew D. Rabdau, Patent Attorney
Sharp Laboratories of America, Inc.
5750 NW Pacific Rim Boulevard
Camas, WA 98607
Telephone: (360) 834-8567
Facsimile: (360) 817-8505

FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER SLA0805		APPLICATION NUMBER	
				APPLICANT Wei Gao, and Yoshi Ono			
				FILING DATE: September 30, 2003		GROUP ART UNIT	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE. DATE IF APPROP.	
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO	
OTHER DOCUMENTS							
	Article entitled: Nb Oxide Thin Film Resistors; by Wilson <i>et al.</i> , published in IEEE Transactions on Applied Superconductivity, Vol.9 No. 2, June 1999.						
	Article entitled: Properties of Ru-Ta Alloys as Gate Electrodes For NMOS and PMOS Silicon Devices, by Zhong <i>et al.</i> , IEEE, 2001						
	Article entitled: Tunable Work Function Molybdenum Gate Technology for FDSOI-CMOS, by Ranade <i>et al.</i> , IEEE 2002						
	Article entitled: A Phase Map for Sputter Deposited Niobium Oxides, by Lee and Aita, pub in the Journal of Applied Physics, Vol. 70, No. 4, 15 August 1991						
EXAMINER				DATE CONSIDERED			